

SANYO	No.4138	2SC4891
	NPN Triple Diffused Planar Silicon Transistor Very High-Definition CRT Display Horizontal Deflection Output Applications	

Features

- High Speed ($t_f=100\text{ns}$ typ).
- High reliability (Adoption of HVP process).
- High breakdown voltage ($V_{CBO}=1500\text{V}$).
- Adoption of MBIT process.

Absolute Maximum Ratings at $T_a = 25^\circ\text{C}$

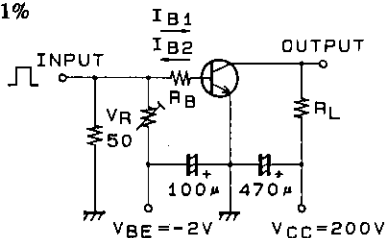
Collector-to-Base Voltage	V_{CBO}	1500	V	
Collector-to-Emitter Voltage	V_{CEO}	800	V	
Emitter-to-Base Voltage	V_{EBO}	6	V	
Collector Current	I_C	15	A	
Peak Collector Current	i_{cp}	35	A	
Collector Dissipation	P_C	3.0	W	
		$T_c = 25^\circ\text{C}$	75	W
Junction Temperature	T_j	150	$^\circ\text{C}$	
Storage Temperature	T_{stg}	-55 to +150	$^\circ\text{C}$	

Electrical Characteristics at $T_a = 25^\circ\text{C}$

			min	typ	max	unit
Collector Cutoff Current	I_{CBO}	$V_{CB}=800\text{V}, I_E=0$			10	μA
Collector Cutoff Current	I_{CES}	$V_{CE}=1500\text{V}, R_{BE}=0$			1.0	mA
Collector Sustain Voltage	$V_{CEO(sus)}$	$I_C=100\text{mA}, I_B=0$	800			V
Emitter Cutoff Current	I_{EBO}	$V_{EB}=4\text{V}, I_C=0$			1.0	mA
C-E Saturation Voltage	$V_{CE(sat)}$	$I_C=12\text{A}, I_B=3.0\text{A}$			5	V
B-E Saturation Voltage	$V_{BE(sat)}$	$I_C=12\text{A}, I_B=3.0\text{A}$			1.5	V
DC Current Gain	$h_{FE(1)}$	$V_{CE}=5\text{V}, I_C=1.0\text{A}$	8		30	
	$h_{FE(2)}$	$V_{CE}=5\text{V}, I_C=12\text{A}$	4		8	
Storage Time	t_{stg}	$I_C=8\text{A}, I_{B1}=1.6\text{A}, I_{B2}=-3.2\text{A}$			3.0	μs
Fall Time	t_f	$I_C=8\text{A}, I_{B1}=1.6\text{A}, I_{B2}=-3.2\text{A}$			0.2	μs

Switching Time Test Circuit

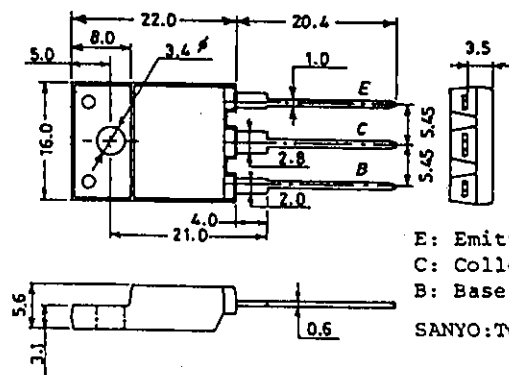
$PW=20\mu\text{s}$
 $DC \leq 1\%$



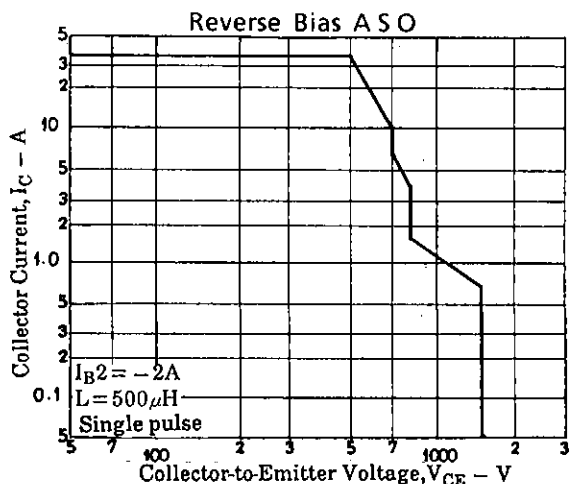
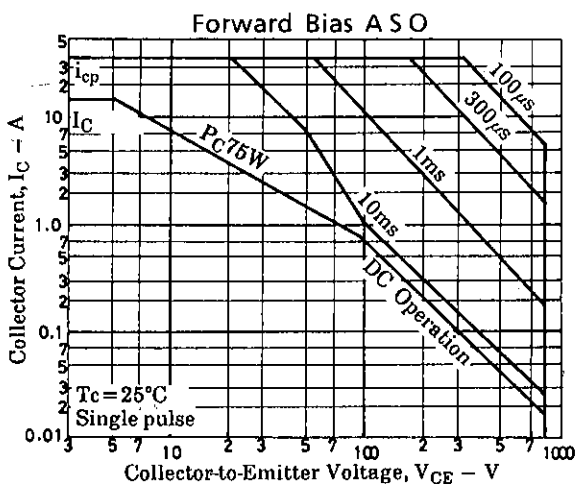
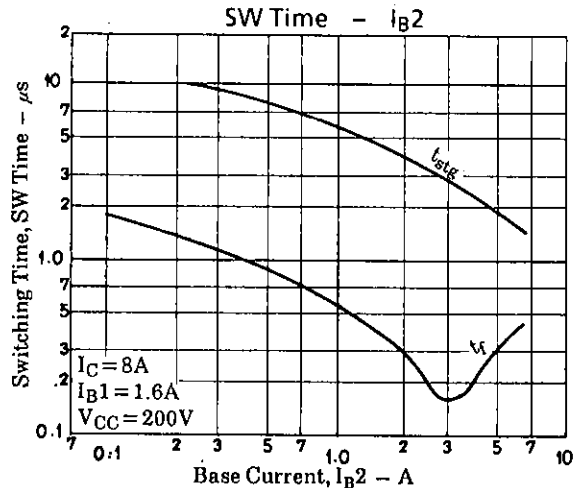
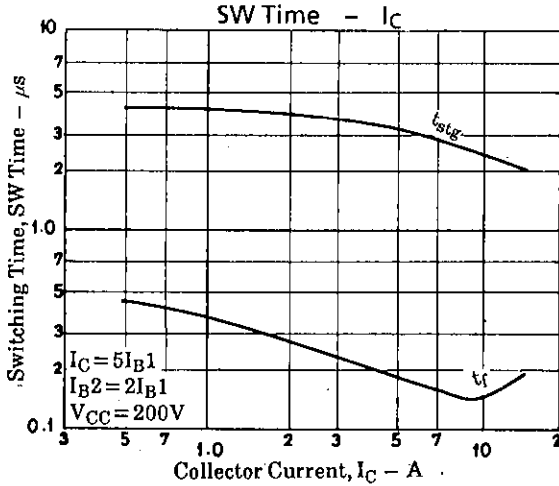
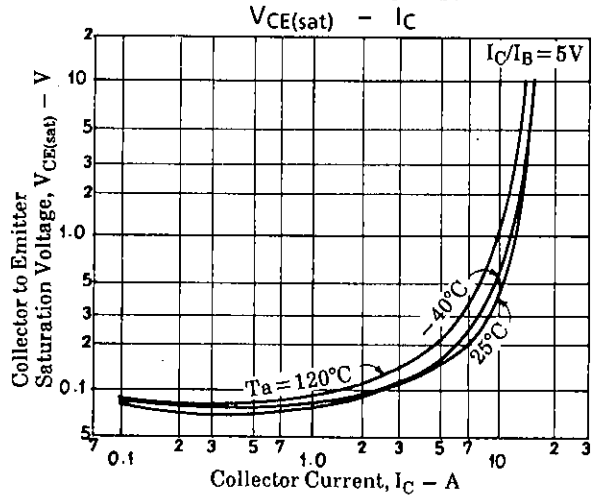
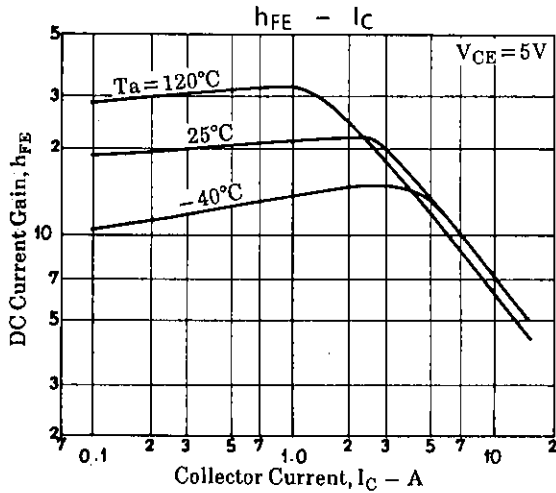
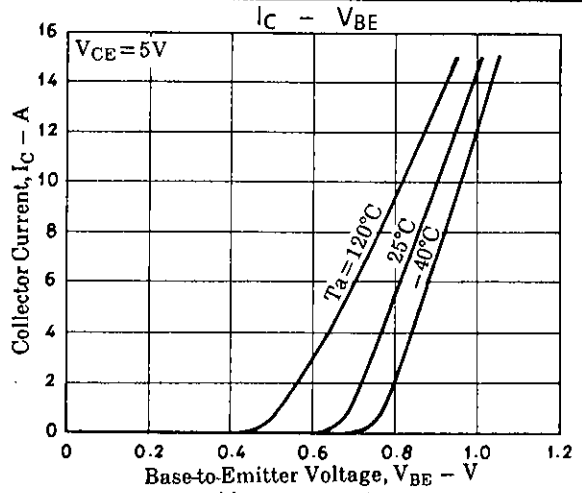
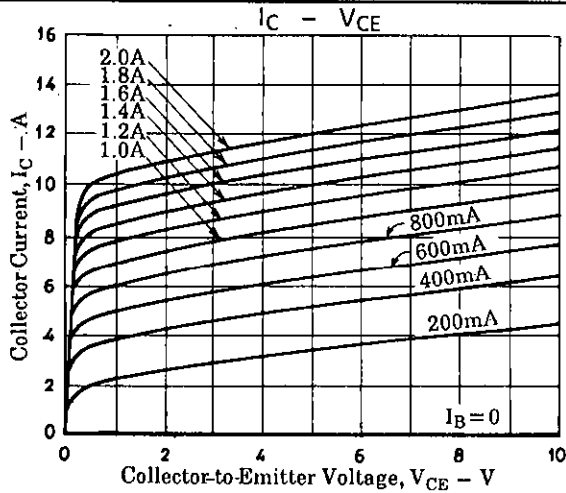
Unit (resistance: Ω , capacitance:F)

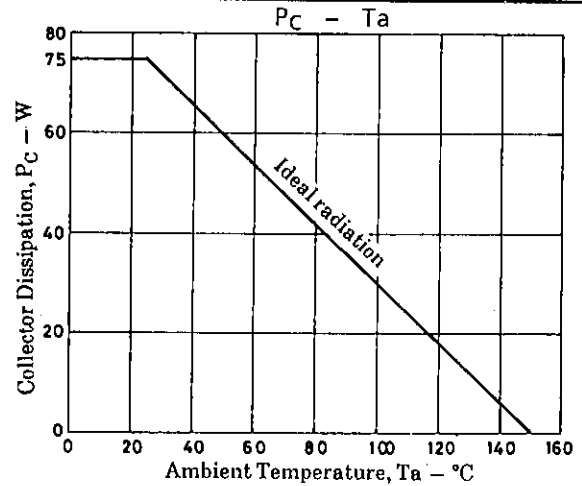
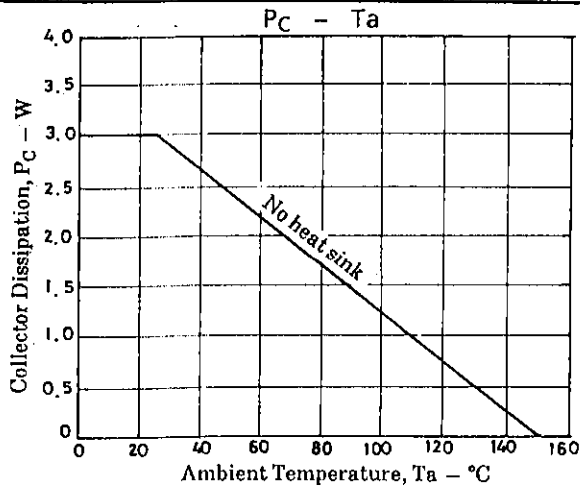
Package Dimensions 2039A

(unit: mm)



E: Emitter
 C: Collector
 B: Base
 SANYO:TO3PML





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